

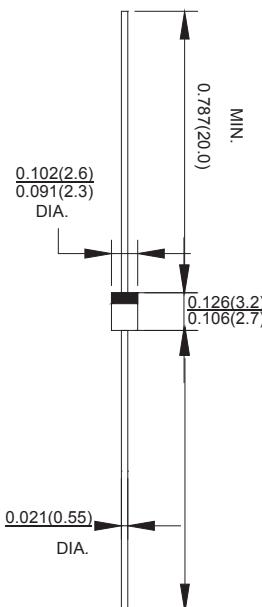
R-1 PLASTIC SILICON RECTIFIERS

FEATURES

- Diffused junction
- Low forward voltage drop
- High current capability
- High reliability
- High surge current capability

MECHANICAL DATA

- Case: JEDEC R-1, molded plastic
- Terminals: Axial lead, solderable per MIL-STD-202, Method 208
- Polarity: Color band denotes cathode
- Mounting position: Any



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	1H1	1H2	1H3	1H4	1H5	1H6	1H7	1H8	UNITS		
Maximum recurrent peak reverse voltage	V _{RRM}	50	100	200	300	400	600	800	1000	V		
Maximum RMS voltage	V _{RMS}	35	70	140	210	280	420	560	700	V		
Maximum DC blocking voltage	V _{DC}	50	100	200	300	400	600	800	1000	V		
Maximum average forward rectified current 9.5mm lead length, @T _A =75°C	I _{F(AV)}	1.0							A			
Peak forward surge current 8.3ms single half-sine-wave superimposed on rated load @T _J =125°C	I _{FSM}	30.0							A			
Maximum instantaneous forward voltage @ 1.0 A	V _F	1.0			1.3		1.7		V			
Maximum reverse current @T _A =25°C at rated DC blocking voltage @T _A =100°C	I _R	5 125.0							μA			
Maximum reverse recovery time (Note1)	t _{rr}	50				75				ns		
Typical junction capacitance (Note2)	C _J	20				15				pF		
Typical thermal resistance (Note3)	R _{θJA}	60							°C/W			
Operating junction temperature range	T _J	- 55 ---- + 150							°C			
Storage temperature range	T _{STG}	- 55 ---- + 150							°C			

NOTE: 1. Measured with I_F=0.5A, I_R=1A, I_{rr}=0.25A.
 2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.
 3. Thermal resistance from junction to ambient.

RATINGS AND CHARACTERISTIC CURVES

FIG.1: Io-Ta Curve

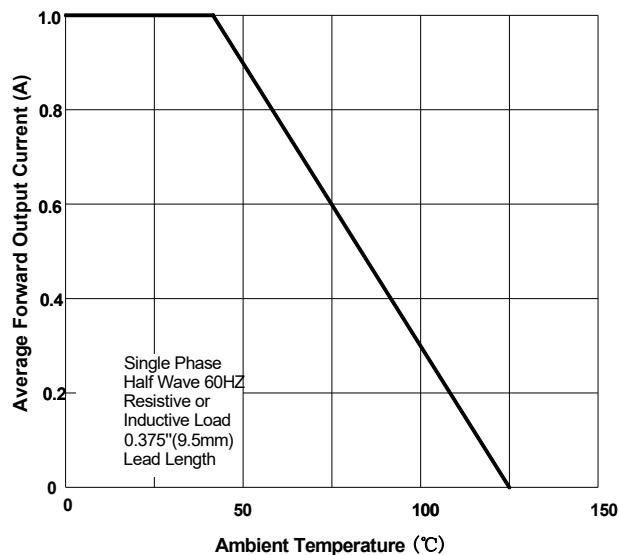


FIG.2: Surge Forward Current Capability

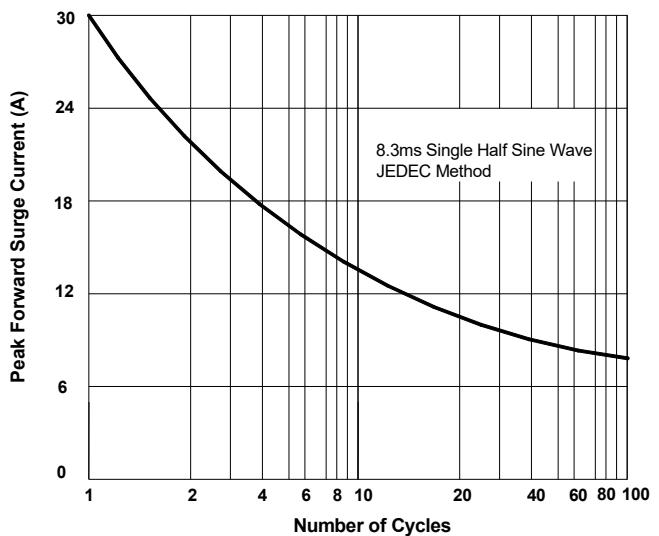


FIG.3: Forward Voltage

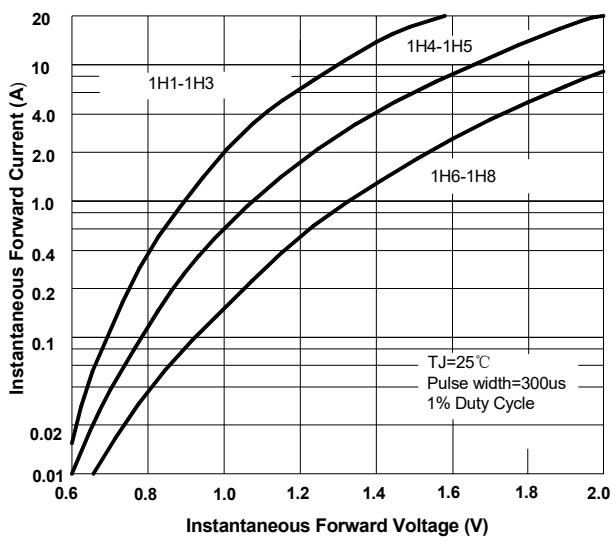


FIG.4: Typical Reverse Characteristics

